First principles calculations within DFT some practical concerns

Ling-Ti Kong

EMail: konglt@sjtu.edu.cn

School of Materials Science and Engineering, Shanghai Jiao Tong University

Nov 16, 2022



Outline

- *k*-sampling
- Plane wave cutoff
- Seudo-potential
- 4 Born-von Karman PBC: look back
- 5 Summary: PP+PW within DFT
- **6** Further readings

Kohn-Sham Equation for crystals

Schrödinger Equation ⇒ Eigen problem

$$\sum_{m} \left[\frac{\hbar^{2} |\mathbf{k} + \mathbf{G}_{m}|^{2}}{2m_{e}} \delta_{m,m'} + v_{m-m'} \right] \mathbf{c}_{i,m} = \epsilon_{i} \mathbf{c}_{i,m'}$$

Matrix equation

(here we have omitted the constants h and m)

Brillouin zone integration

Properties like the electron density, total energy, etc., can be evaluated by integration over the first Brillouin zone.

Electron density

$$n(\mathbf{r}) = \frac{1}{\Omega_{FBZ}} \sum_{i}^{occ.} \int_{FBZ} n_{i,\mathbf{k}}(\mathbf{r}) d\mathbf{k}, \qquad n_{i,\mathbf{k}}(\mathbf{r}) = |\psi_{i,\mathbf{k}}(\mathbf{r})|^{2}$$

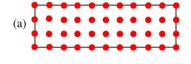
$$= \frac{1}{\Omega_{FBZ}} \sum_{i} \int_{FBZ} f_{i,\mathbf{k}} \cdot n_{i,\mathbf{k}}(\mathbf{r}) d\mathbf{k}$$

$$= \frac{1}{N_{k}} \sum_{\mathbf{k}} \sum_{i} f_{i,\mathbf{k}} \cdot n_{i,\mathbf{k}}(\mathbf{r})$$

k-point sampling: uniform vs non-uniform

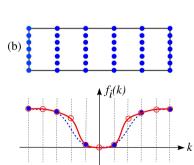
Moreno and Soler (Phys. Rev. B 45(24):13891, 1992):

A mesh with uniformly distributed k-points is preferred.



Example: A rectangular lattice

- (a) isotropic sampling
- (b) finer sampling vertically poor sampling horizontally



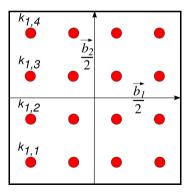
Monkhorst-Pack scheme

Monkhorst & Pack (Phys. Rev. B 13:5188, 1976.):

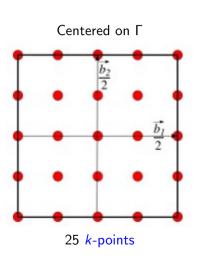
$$\mathbf{k} = \sum_{i=1}^{3} \frac{2n_i - N_i - 1}{2N_i} \mathbf{b}_i, \quad n_i = 1, \dots, N_i$$

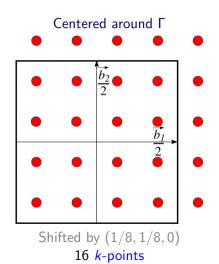
Example: $4 \times 4 \times 1$ MP mesh for 2D square lattice

$$k_{1,1} = \left(-\frac{3}{8}, -\frac{3}{8}\right)$$
 $k_{1,3} = \left(-\frac{3}{8}, \frac{1}{8}\right)$
 $k_{1,2} = \left(-\frac{3}{8}, -\frac{1}{8}\right)$ $k_{1,4} = \left(-\frac{3}{8}, \frac{3}{8}\right)$



Shifted Monkhorst-Pack mesh





Yet the same k-point density.

Symmetry on **k** in the first Brillouin zone

$$\psi_{\mathbf{k}+\mathbf{G}} = \psi_{\mathbf{k}} \Rightarrow \text{Limit } \mathbf{k} \text{ in FBZ}.$$

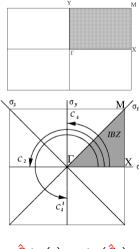
$$\left[-\frac{\hbar^2}{2m_e} \bigtriangledown^2 + v_{eff}(\mathbf{r}) \right] u_{\mathbf{k}}(\mathbf{r}) e^{i\mathbf{k}\mathbf{r}} = \epsilon u_{\mathbf{k}}(\mathbf{r}) e^{i\mathbf{k}\mathbf{r}}
\left[-\frac{\hbar^2}{2m_e} \bigtriangledown^2 + v_{eff}(\mathbf{r}) \right] u_{\mathbf{k}}^*(\mathbf{r}) e^{-i\mathbf{k}\mathbf{r}} = \epsilon u_{\mathbf{k}}^*(\mathbf{r}) e^{-i\mathbf{k}\mathbf{r}} \quad \text{Congugate}
\left[-\frac{\hbar^2}{2m_e} \bigtriangledown^2 + v_{eff}(\mathbf{r}) \right] u_{-\mathbf{k}}^*(\mathbf{r}) e^{i\mathbf{k}\mathbf{r}} = \epsilon u_{-\mathbf{k}}^*(\mathbf{r}) e^{i\mathbf{k}\mathbf{r}} \quad \text{replace } \mathbf{k} \text{ by } -\mathbf{k}$$

$$u_{-\mathbf{k}}^* = u_{\mathbf{k}} \implies u_{-\mathbf{k}} = u_{\mathbf{k}}^*$$

$$\psi_{-\mathbf{k}} = u_{-\mathbf{k}}e^{-i\mathbf{k}\mathbf{r}} = \left(u_{\mathbf{k}}e^{i\mathbf{k}\mathbf{r}}\right)^* = \psi_{\mathbf{k}}^*$$

$$\epsilon_{-\mathbf{k}} = \epsilon_{\mathbf{k}}$$

Symmetry on **k** in the first Brillouin zone



$$\hat{\mathbf{S}}\psi_{i\mathbf{k}}(\mathbf{r}) = \psi_{i\mathbf{k}}(\hat{\mathbf{S}}\mathbf{r})$$

$$\hat{S}\psi_{i\mathbf{k}}(\mathbf{r}) = \psi_{i\mathbf{k}}(\hat{S}\mathbf{r})
= u_{i\mathbf{k}}(\hat{S}\mathbf{r})e^{i\mathbf{\tilde{S}}\mathbf{k}\cdot\hat{S}\mathbf{r}}
= u_{i\mathbf{k}}(\mathbf{r})e^{i\mathbf{k}'\mathbf{r}}$$

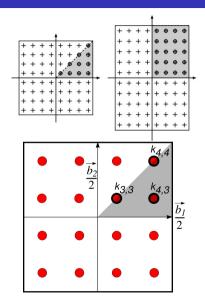
 $\psi_k(r)$ is a solution at $k \Longrightarrow \psi(\hat{S}r)$ is a solution at $\check{S}k$, with same energy/density.

$$n(\mathbf{r}) = \sum_{\mathbf{k}} \omega_{\mathbf{k}} \sum_{i} f_{i,\mathbf{k}} \cdot n_{i,\mathbf{k}}(\mathbf{r})$$

k ∈ irreducible Brillouin zone

$$\omega_{k} = \frac{\text{# of sym. connected } k}{\text{total # of } k \text{ in FBZ}}$$

Irreducible Brillouin zone



Example:

MP-mesh for 2D square lattice

 $4 \times 4 \times 1$ MP mesh = 16 k-points in the FBZ.

• 4 equivalent
$$k_{4,4} = (\frac{3}{8}, \frac{3}{8}) \Rightarrow w_1 = 0.25$$

• 4 equivalent
$$k_{3,3} = (\frac{1}{8}, \frac{3}{8}) \Rightarrow w_2 = 0.25$$

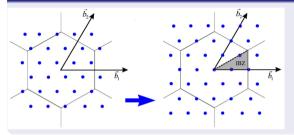
• 8 equivalent
$$k_{4,3} = (\frac{3}{8}, \frac{1}{8}) \Rightarrow w_3 = 0.50$$

Brillouin zone integration

$$n(r) = \frac{1}{4} \sum_{i}^{occ.} n_{i,k_{4,4}} + \frac{1}{4} \sum_{i}^{occ.} n_{i,k_{3,3}} + \frac{1}{2} \sum_{i}^{occ.} n_{i,k_{4,3}}$$

Irreducible Brillouin zone

Symmetry break: Hexagonal cell

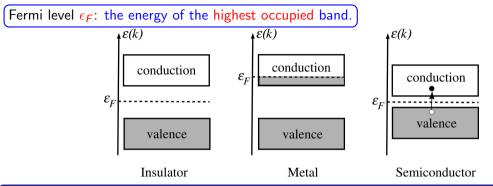


Even meshes break the symmetry, while meshes centered on Γ preserves it. Shift the k-point mesh to preserve hexagonal symmetry!

k-sampling: rules of thumb

- Keep density of k constant in each direction: $\frac{\mathbf{b}_i}{N_i} = const.$
- Denser $k \Rightarrow$ more precise results.
- N_k^{IBZ} does not necessarily scale with N. Symmetry matters
- No k sampling needed for atoms or molecules!
- Generally need to do convergence test!

Smearing method: fractional occupation numbers



IBZ integration over the filled states: Occupation number

$$f_{i,\mathbf{k}} = \Theta(\epsilon_{i\mathbf{k}} - \epsilon_F), \qquad \Theta(x) = \begin{cases} 1 & x \leq 0 \\ 0 & x > 0 \end{cases}$$

For insulators and semiconductors, DOS goes to zero smoothly at the gap.

For metals, the resolution of the step function at ϵ_F is very sensitive.

Smearing method: fractional occupation numbers

Trick is to replace sharp step function with a smoother function allowing partial occupancies at the Fermi level.

• Fermi-Dirac smearing

$$f_{i\mathbf{k}} = \frac{1}{1 + \exp(x)}, \qquad x = \frac{\epsilon_{i\mathbf{k}} - \epsilon_F}{\sigma}, \qquad \sigma = k_B T$$

Gaussian smearing

$$ext{erf}(x) = \frac{2}{\sqrt{\pi}} \int_0^x e^{-t^2} dt$$

$$f_{i\mathbf{k}} = \frac{1}{2} [1 - \operatorname{erf}(x)],$$
 σ has no physical meaning.

Methfessel-Paxton smearing

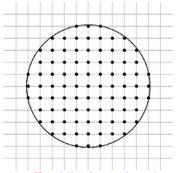
$$\delta(x) \simeq D_N(x) = \sum_{n=1}^{N} A_n H_{2n} e^{-x^2}; \qquad f_{i\mathbf{k}} \simeq S_N = 1 - \int_{-\infty}^{x} D_N(\tau) d\tau$$

Cutoff: finite basis set

Computationally, a complete expansion in terms of infinitely many plane waves is not possible. The coefficients, $c_{i,m}(\mathbf{k})$ decrease rapidly with increasing PW kinetic energy $\frac{\hbar^2 |\mathbf{k} + \mathbf{G}_m|^2}{2m}$.

A cutoff energy value, $E_{\rm cut}$, determines the number of PWs ($N_{\rm pw}$) in the expansion, satisfying,

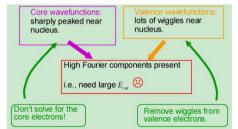
$$\frac{\hbar^2 |\mathbf{k} + \mathbf{G}_m|^2}{2m} < E_{\mathrm{cut}}$$

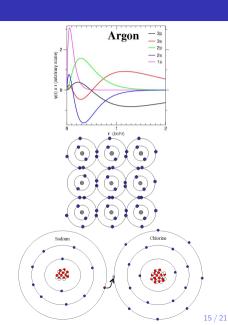


 $N_{\rm pw}$ is a discontinuous function of the PW kinetic energy cutoff, while depends only on the computational cell size and the cutoff energy value.

Pseudopotential: why?

- Reduction of basis set size effective speedup of calculation
- Reduction of number of electrons reduces the number of d.o.f.
- UnnecessaryWhy bother? They are inert anyway···
- Inclusion of relativistic effects relativistic effects can be included partially

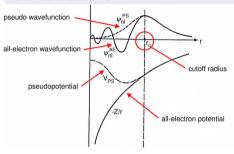




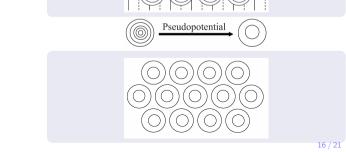
Pseudopotential: how?

Pseudopotential (PP)

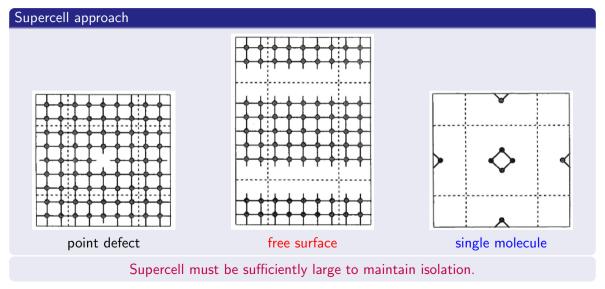
A smooth effective potential that reproduces the effect of the nucleus plus core electrons on valence electrons.



- Norm conserving PP;
- Ultrasoft PP;
- Projector Augmented Wave PP;



Born-von Karman PBC: always a necessity?



DFT: Ability and disability

Fundamentally, DFT can only predict the ground state electronic density and the ground state total energy of a set of electrons under an external potential.

DFT can predict

- Total energy
- Forces
- Lattice constants
- Bond lengths
- Vibrational frequencies
- Phonon frequencies
- Electron density
- Static dielectric response

DFT cannot predict

- Excited state energies
- Band gap
- Band structures
- Wave functions
- Fermi surface
- Superconductivity
- Excitons
- Electronic transport

Accuracy

Accuracies can be expected

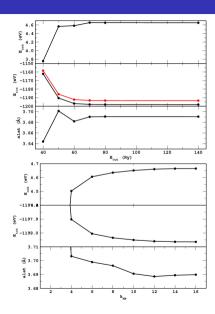
```
bond length \sim 3\% too small bulk modulus \sim 10\% too high phonon frequency energy difference cohesive energy very poor (much too high)
```

Accuracies for properties that DFT technically does not predict

band gap 50% too small qualitatively reasonable fermi surface qualitatively reasonable

Influencing factors

- Born-Oppenheimer approximation;
- Density functional theory
 - LDA, GGA
 - LSDA
- Pseudopotential
- Kinetic energy cutoff
- k-sampling
- convergence criterion
- · · ·



References and further readings

- http://www.fhi-berlin.mpg.de/th/Meetings/FHImd2001/pehlke1.pdf
- 4 http://itp.tugraz.at/LV/ewald/TFKP/Literatur_Pseudopotentiale/Roundy_05_DFT+PPsumm.pdf
- http://www.phys.sinica.edu.tw/TIGP-NANO/Course/2007_Spring/Class%20Notes/CMS.20070531.pseudo.pdf
- J. Singleton, Band theory and electronic properties of solids, Oxford University press.
- http://cms.mpi.univie.ac.at/vasp/
- http://www.quantum-espresso.org/
- http://www.abinit.org/
- http://www.cpmd.org/
- http://www.icmab.es/siesta/
- http://abacus.ustc.edu.cn/index.html